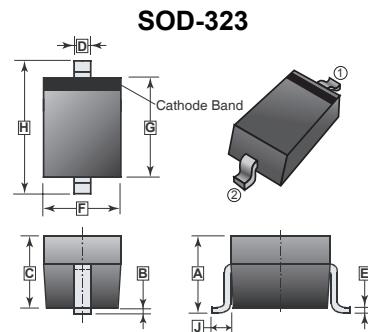


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

- Fast Switching Speed
- Surface Mount Package Ideally Suited for automatic Insertion
- For General Purpose Switching Applications
- High Conductance



MARKING

T6 & T4

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.05	REF.	E	0.080	0.180
B	0.20	REF.	F	1.15	1.45
C	0.80	1.00	G	1.60	1.80
D	0.25	0.40	H	2.30	2.70

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Single diode @ $T_A = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}		
Working Peak Reverse Voltage	V_{RWM}	75	V
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Peak Forward Surge Current @=1.0μs @=1.0s	I_{FSM}	2.0 1.0	A
Power Dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	K/W
Junction, Storage Temperature	T_J, T_{STG}	125, -65 ~ +150	°C

ELECTRICAL CHARACTERISTICS (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameters	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Voltage Leakage Current	I_R	-	1 25	μA nA	$V_R = 75\text{V}$ $V_R = 20\text{V}$
Forward Voltage	V_{F1}	-	715	mV	$I_F = 1\text{mA}$
	V_{F2}	-	855		$I_F = 10\text{mA}$
	V_{F3}	-	1000		$I_F = 50\text{mA}$
	V_{F4}	-	1250		$I_F = 150\text{mA}$
Diode Capacitance	C_T	-	2.0	pF	$V_R = 0, f=1\text{MHz}$
Reverse Recovery Time	t_{RR}	-	4	nS	$I_F = I_R = 10\text{ mA}$, $I_{RR}=0.1 \times I_R$, $R_L=100\Omega$

RATINGS AND CHARACTERISTIC CURVES

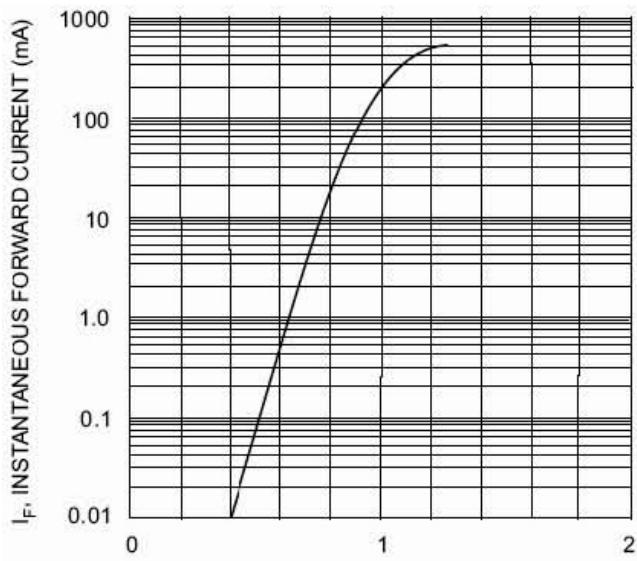


Fig. 1 Forward Characteristics

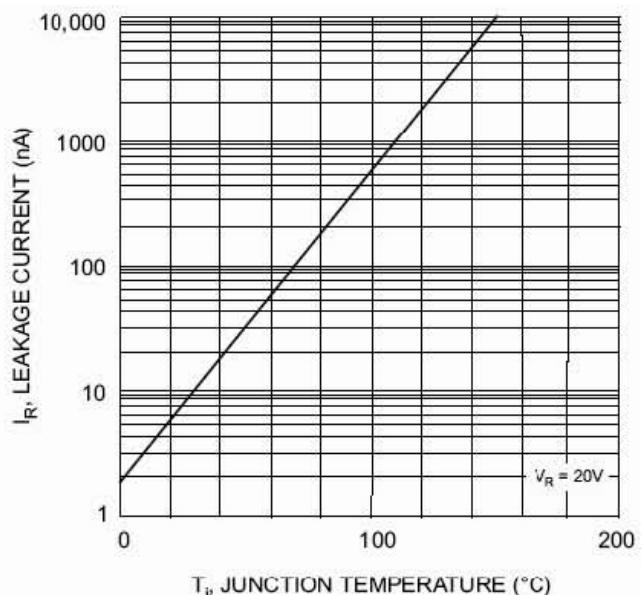


Fig. 2 Leakage Current vs Junction Temperature